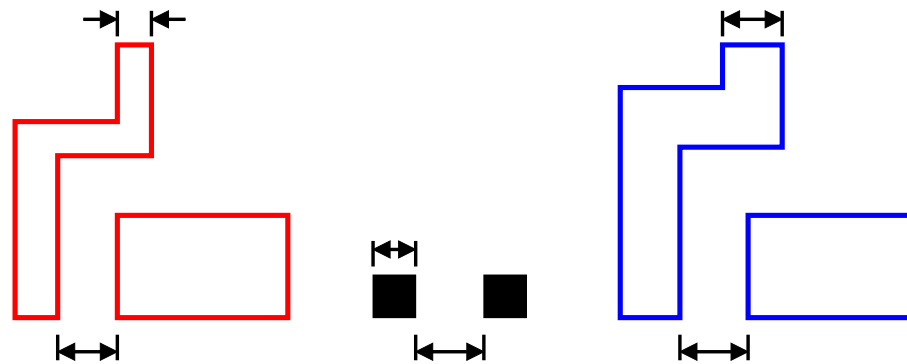


# Design Rules

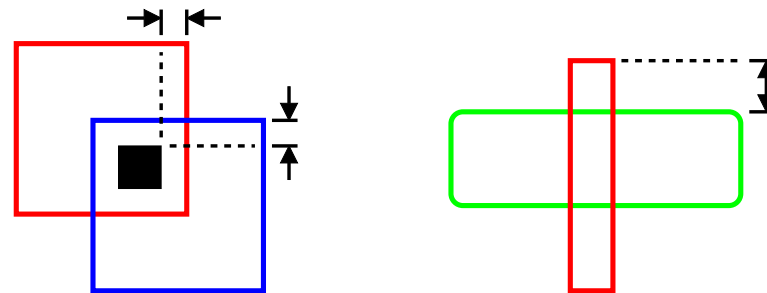
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To prevent chip failure, designs must conform to design rules:

- Single layer rules



- Multi-layer rules



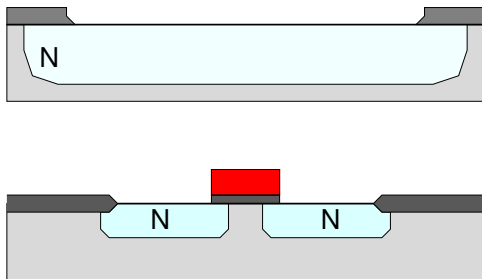
# Derivation of Design Rules

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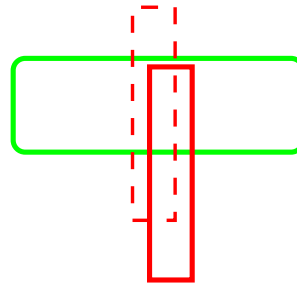
Isotropic Etching



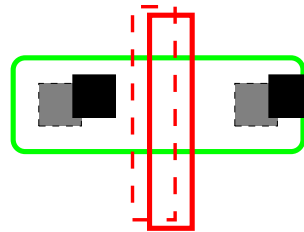
Lateral Diffusion



Mask Misalignment

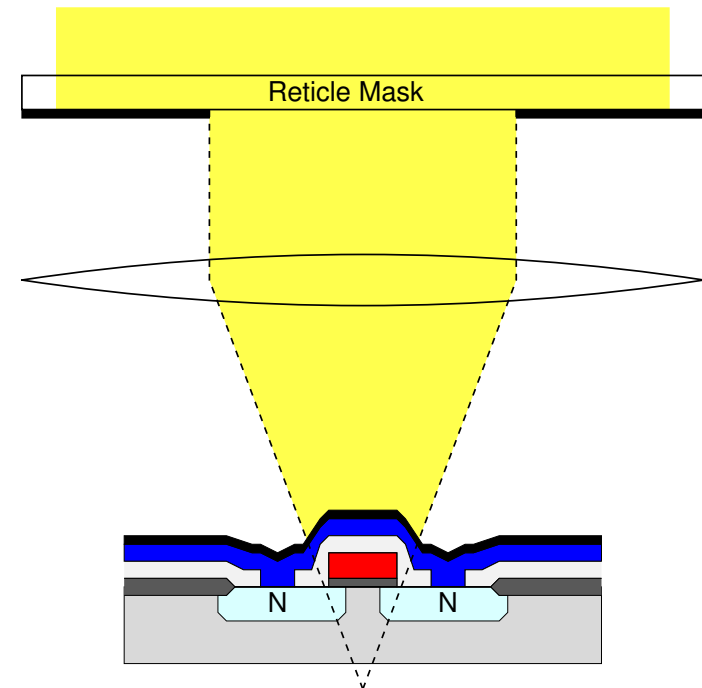


Misalignment can be Cumulative



□ is aligned to ○  
■ is aligned to □

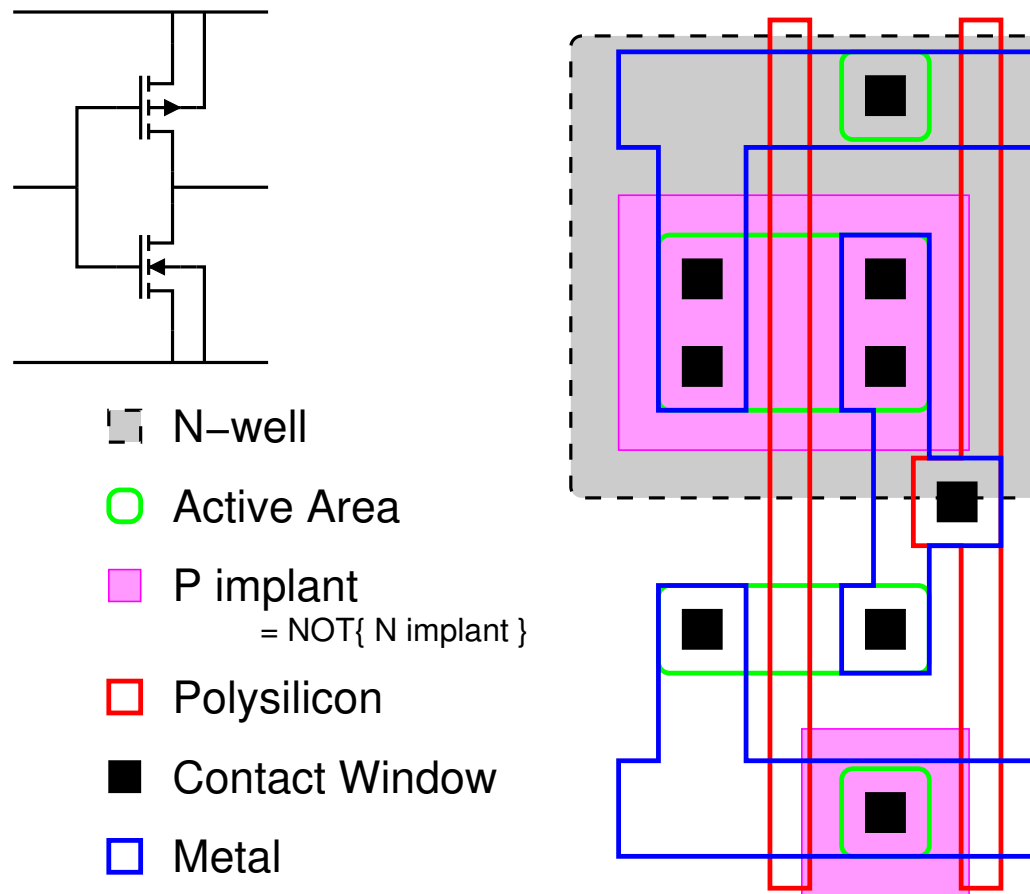
Optical Focus over 3D terrain



# Design Rules

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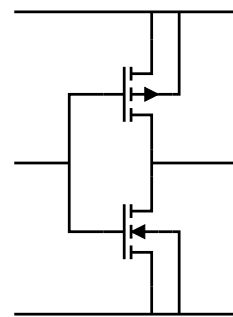
## 0.5 $\mu m$ CMOS inverter



# Design Rules

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## 0.5 $\mu\text{m}$ CMOS inverter



□ N-well

○ Active Area

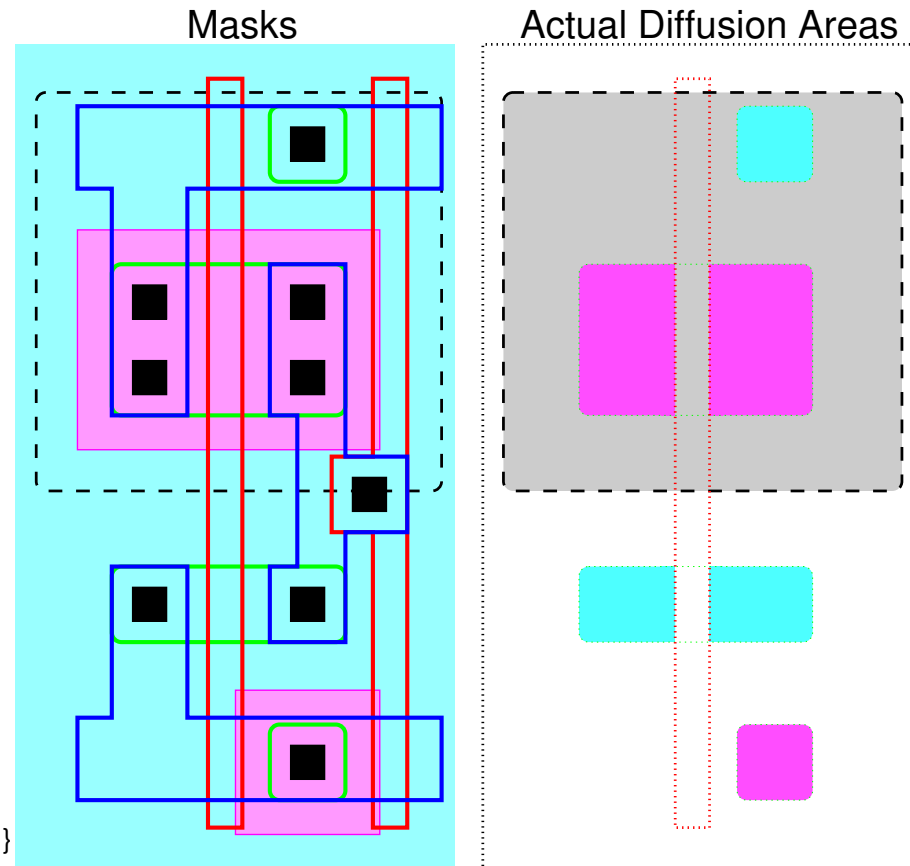
■ P implant

□ Polysilicon

■ Contact Window

□ Metal

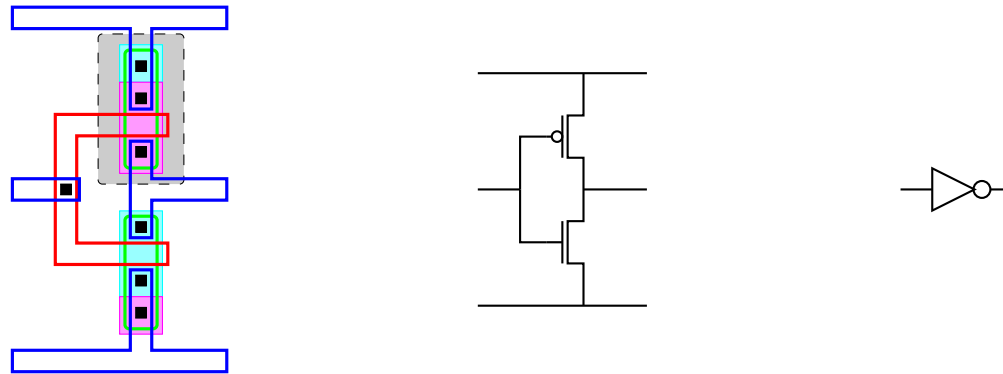
■ N implant = NOT{ P implant }



# Abstraction

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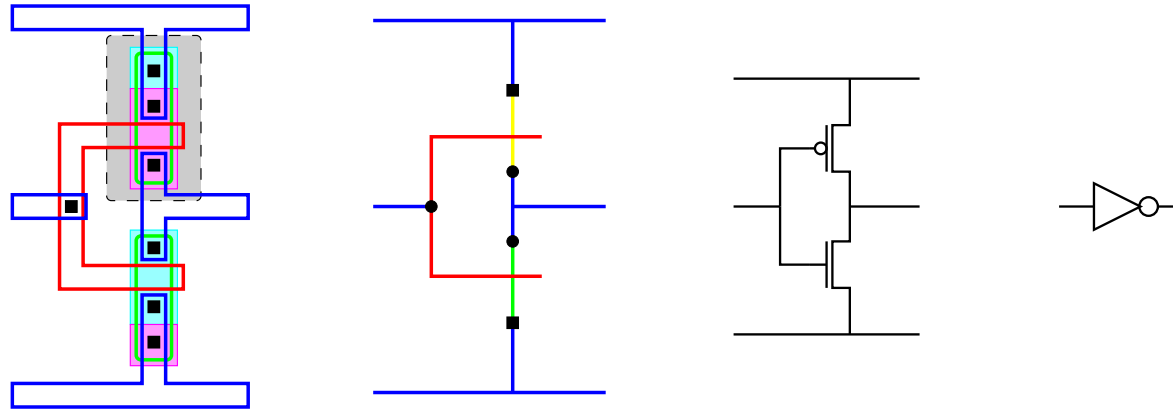
## Levels of Abstraction



- Mask Level Design
  - Laborious Technology/Process dependent.
  - Design rules may change during a design!
- Transistor Level Design
  - Process independent, Technology dependent.
- Gate Level Design
  - Process/Technology independent.

# Abstraction - Stick Diagrams

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Stick diagrams give us many of the benefits of abstraction:

- Much easier/faster than full mask specification.
- Process independent (valid for any CMOS process).
- Easy to change.

while avoiding some of the problems:

- Optimized layout may be generated much more easily from a stick diagram than from transistor or gate level designs.<sup>1</sup>

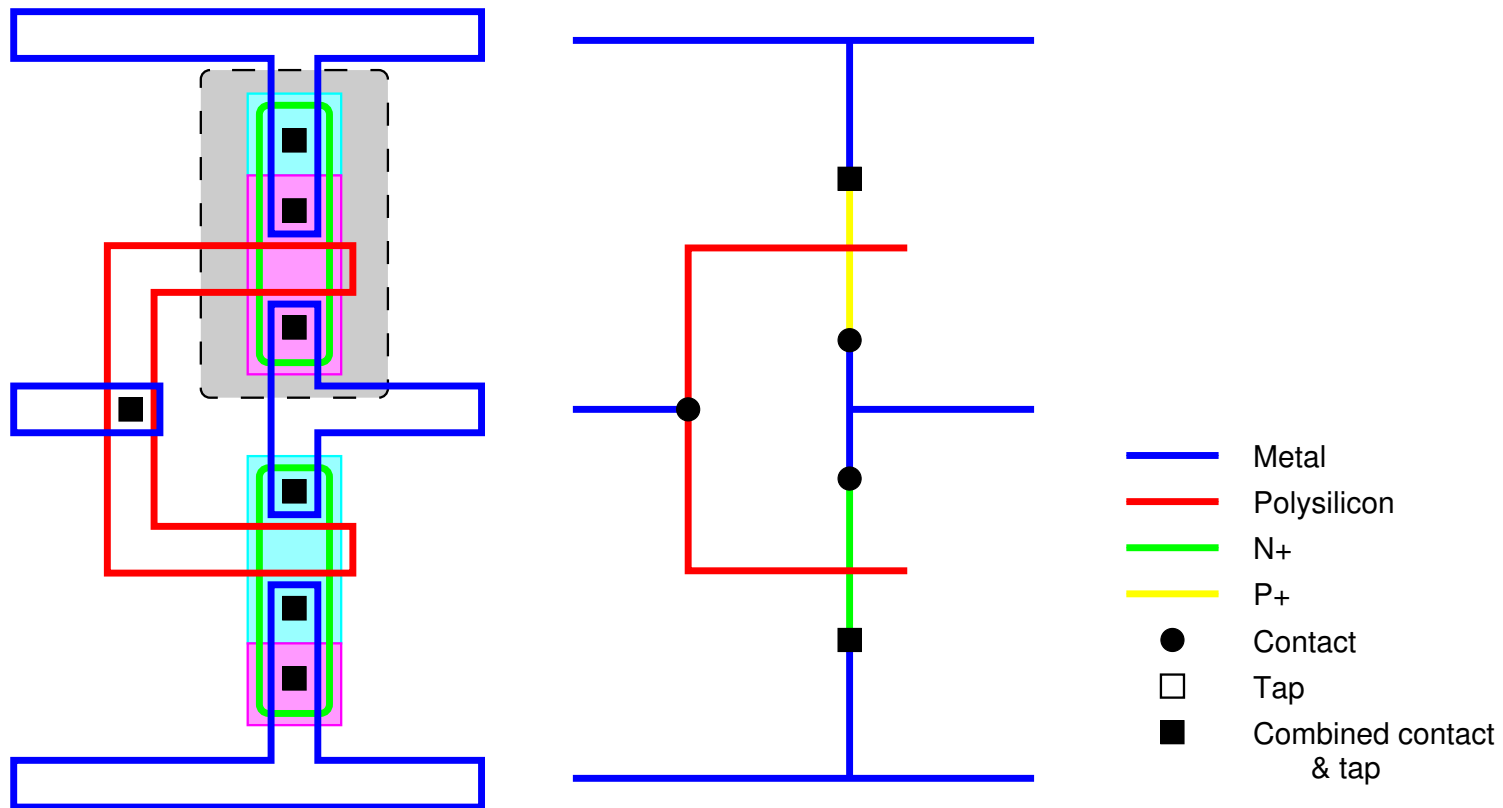
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<sup>1</sup>note that all IC designs must end at the mask level.

# Digital CMOS Design

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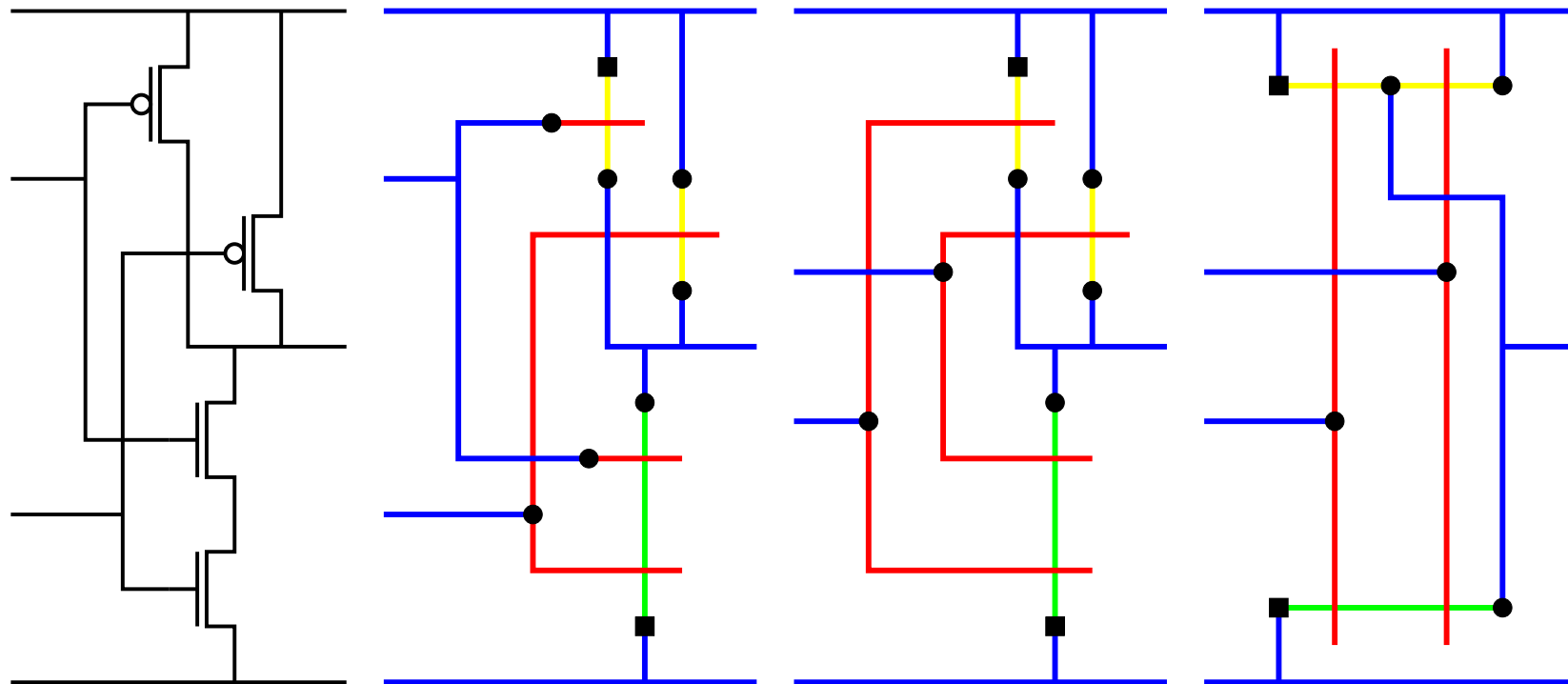
## Stick Diagrams



# Digital CMOS Design

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## Stick Diagrams





# Digital CMOS Design

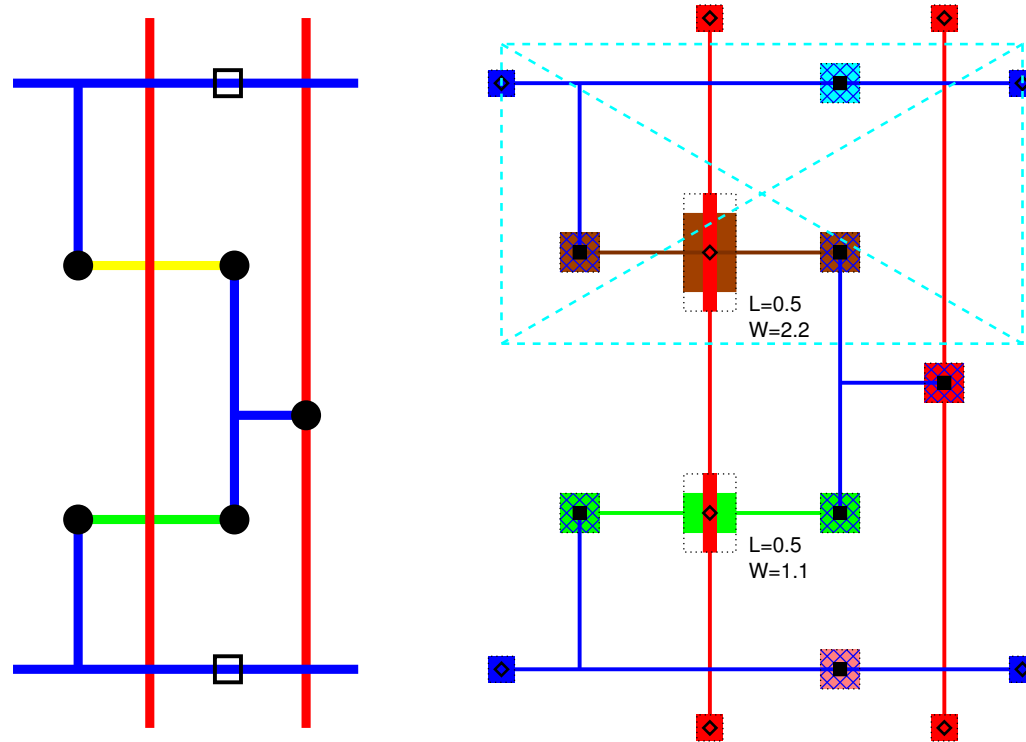
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## Stick Diagrams

- *Explore your Design Space.*
  - Implications of crossovers.
  - Number of contacts.
  - Arrangement of devices and connections.
- Process independent layout.
- Easy to expand to a full layout for a particular process.

# Sticks and CAD - Symbolic Capture

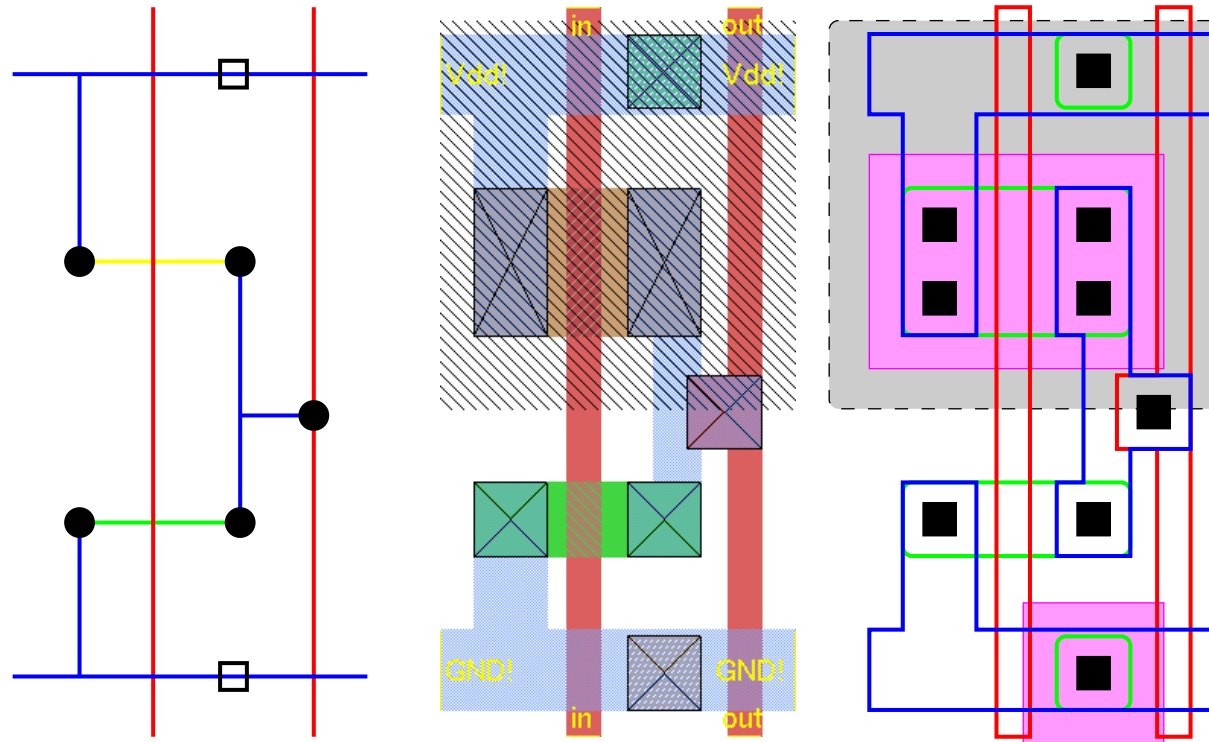
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- Transistors are placed and explicitly sized.
  - components are joined with zero width wires.
  - contacts are automatically selected as required.
- A semi-automatic compaction process will create DRC correct layout.

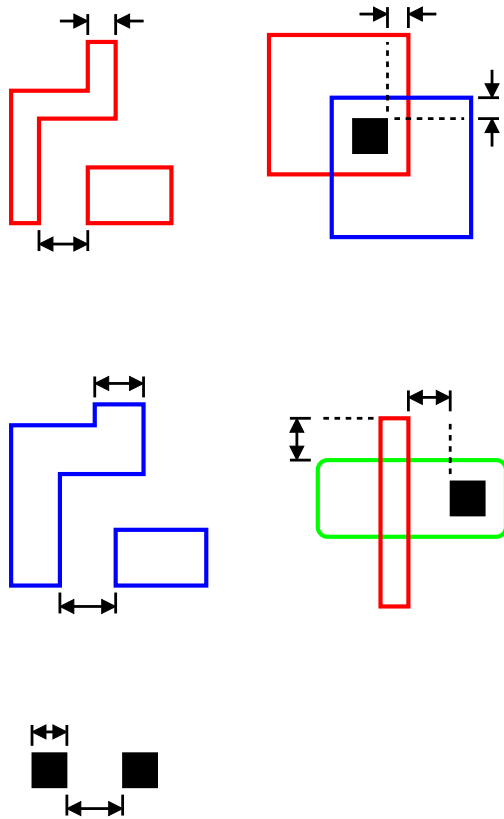
# Sticks and CAD - Magic

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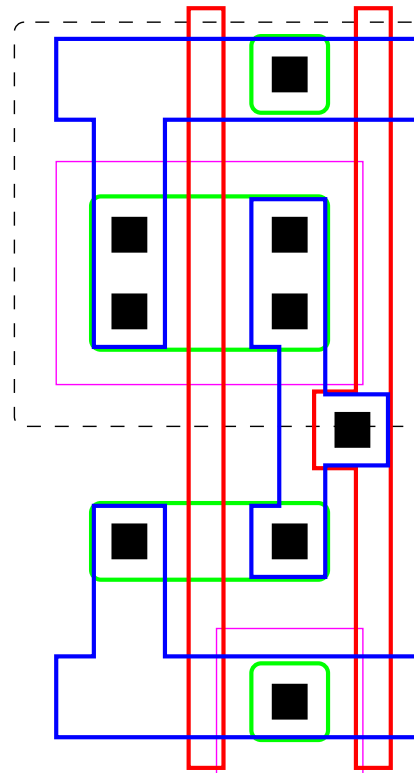


- Log style design (sticks with width) - DRC errors are flagged immediately.
  - again contacts are automatically selected as required.
- On-line DRC leads to rapid generation of correct designs.
  - symbolic capture style compaction is available if desired.

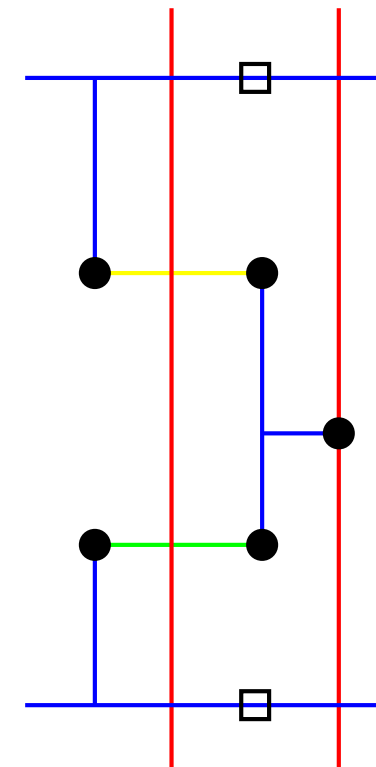
Design Rules – width, separation, overlap



Optimised Mask Layout



Equivalent Stick Diagram



- Metal
- Polysilicon
- N+
- P+
- Contact
- Tap
- Combined contact & tap